



SamHop Microelectronics Corp.

STU/D302S

Apr 03,2006

N-Channel Logic Level Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V _{DSS}	I _D	R _{DSON} (mΩ) Max
30V	50 A	9 @ V _{GS} = 10V
		12 @ V _{GS} = 4.5V

FEATURES

- Super high dense cell design for low R_{DSON}.
- Rugged and reliable.
- TO-252 and TO-251 Package.



ABSOLUTE MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous @ T _C =25°C -Pulsed ^a	I _D	50	A
	I _{DM}	180	A
Drain-Source Diode Forward Current	I _S	20	A
Maximum Power Dissipation @ T _C =25°C	P _D	50	W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to 175	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	R _{θJC}	3	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	50	°C/W

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ELECTRICAL CHARACTERISTICS ($T_c=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24V, V_{GS}=0V$			1	μA
Gate-Body Leakage	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
ON CHARACTERISTICS ^a						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.7	3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$		7	9	m ohm
		$V_{GS}=4.5V, I_D=10A$		10	12	m ohm
On-State Drain Current	$I_{D(ON)}$	$V_{DS}=10V, V_{GS}=10V$	50			A
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=10A$		22		S
DYNAMIC CHARACTERISTICS ^b						
Input Capacitance	C_{ISS}	$V_{DS}=15V, V_{GS}=0V$ $f=1.0MHz$		1020		pF
Output Capacitance	C_{OSS}			325		pF
Reverse Transfer Capacitance	C_{RSS}			225		pF
Gate resistance	R_g	$V_{GS}=0V, V_{DS}=0V, f=1.0MHz$		0.25		ohm
SWITCHING CHARACTERISTICS ^b						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD}=15V$ $I_D=1A$ $V_{GS}=10V$ $R_{GEN}=6\text{ ohm}$		18		ns
Rise Time	t_r			33		ns
Turn-Off Delay Time	$t_{D(OFF)}$			37		ns
Fall Time	t_f			28		ns
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=20A, V_{GS}=10V$		26		nC
		$V_{DS}=15V, I_D=20A, V_{GS}=4.5V$		13		nC
Gate-Source Charge	Q_{gs}	$V_{DS}=15V, I_D=20A$ $V_{GS}=10V$		2.3		nC
Gate-Drain Charge	Q_{gd}			8.2		nC

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ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS ^a						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_s = 10A$		0.83	1.3	V

Notes

a.Pulse Test:Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.

b.Guaranteed by design, not subject to production testing.

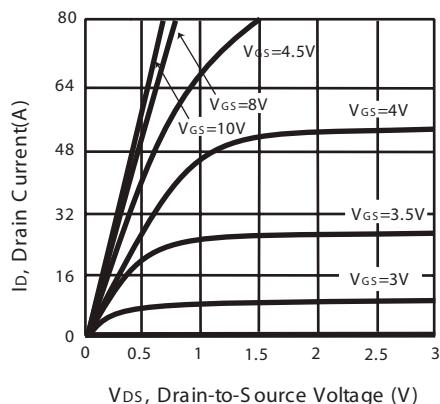


Figure 1. Output Characteristics

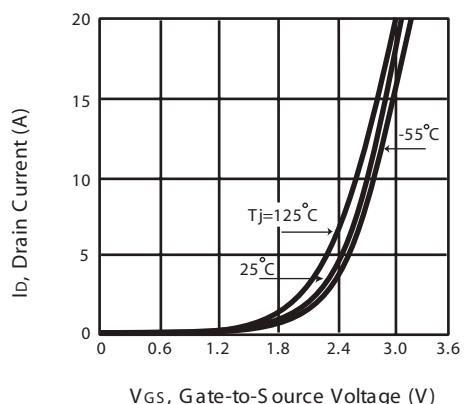


Figure 2. Transfer Characteristics

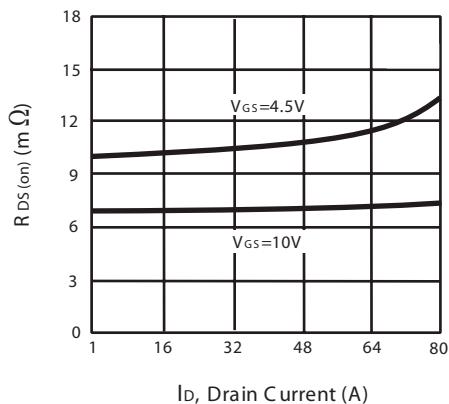


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

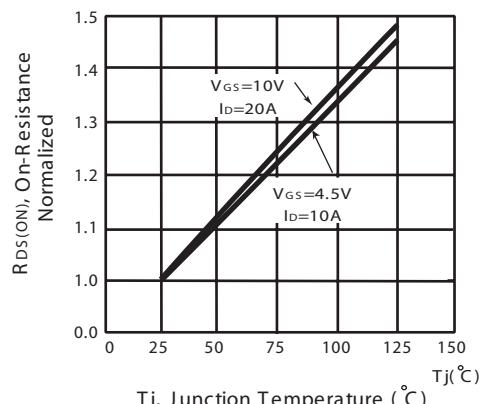


Figure 4. On-Resistance Variation with Drain Current and Temperature

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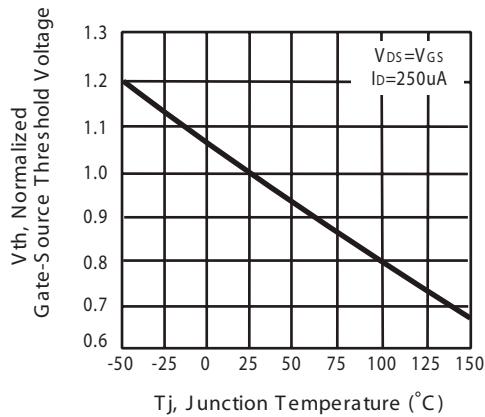


Figure 5. Gate Threshold Variation with Temperature

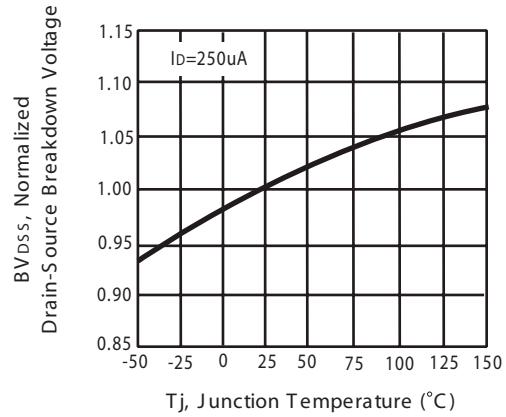


Figure 6. Breakdown Voltage Variation with Temperature

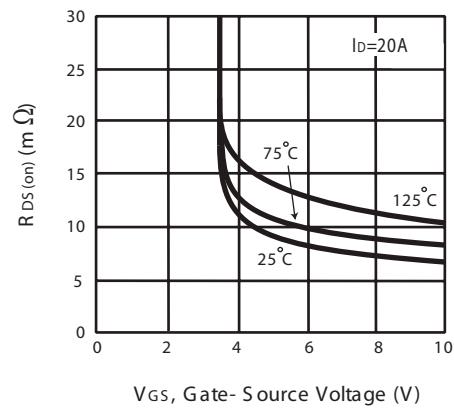


Figure 7. On-Resistance vs. Gate-Source Voltage

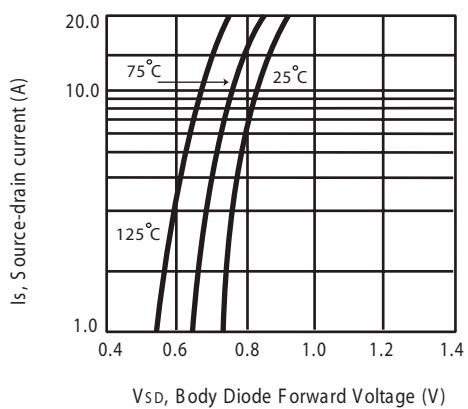


Figure 8. Body Diode Forward Voltage Variation with Source Current

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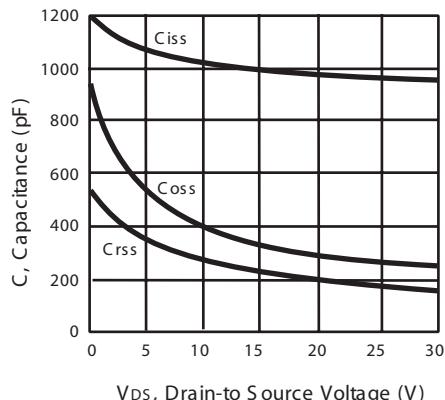


Figure 9. Capacitance

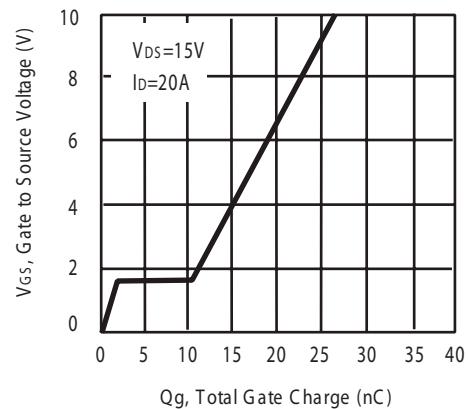


Figure 10. Gate Charge

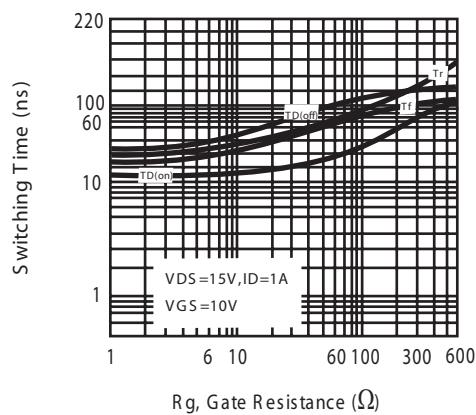


Figure 11. switching characteristics

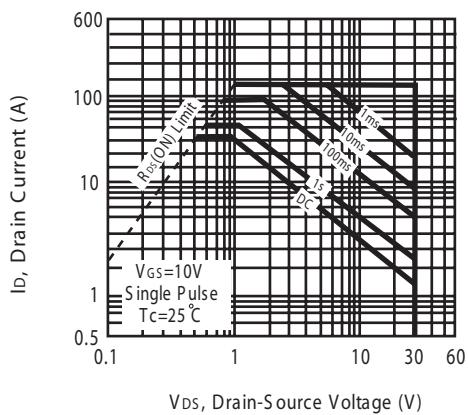


Figure 12. Maximum Safe Operating Area

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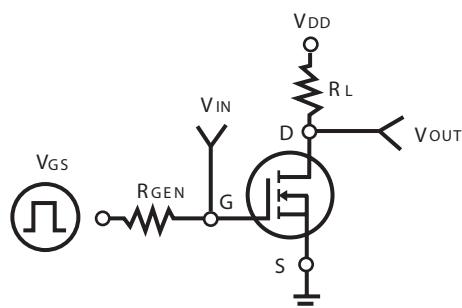


Figure 13. S switching Test Circuit

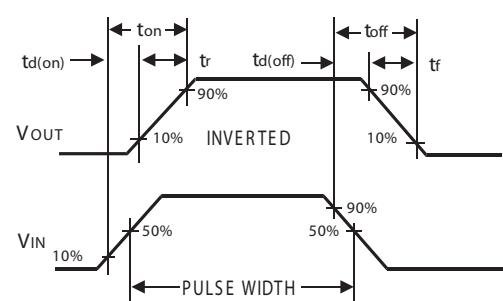


Figure 14. S switching Waveforms

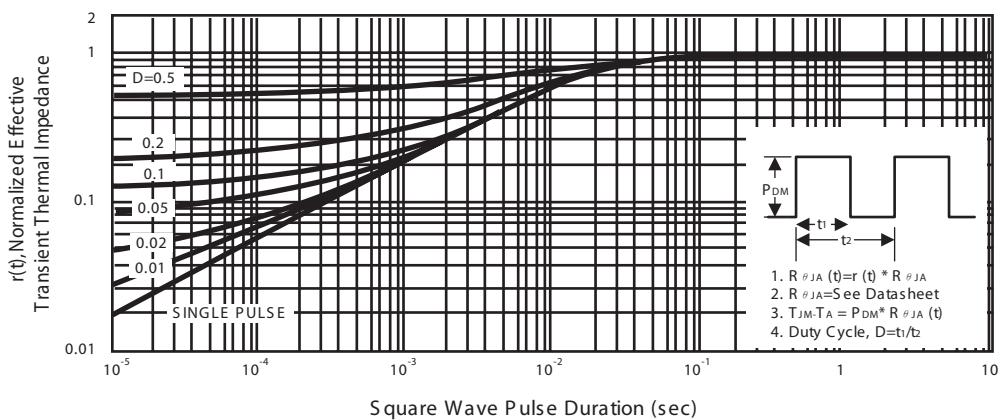
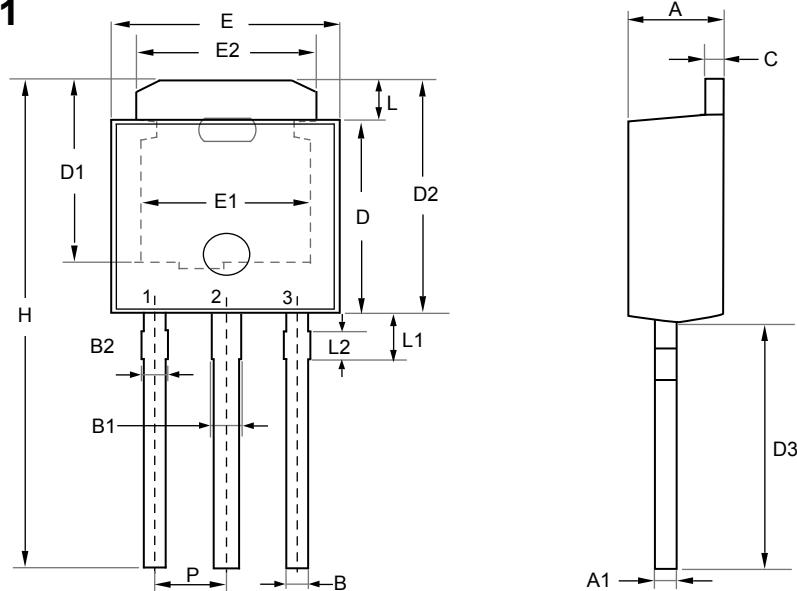


Figure 15. Normalized Thermal Transient Impedance Curve

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PACKAGE OUTLINE DIMENSIONS

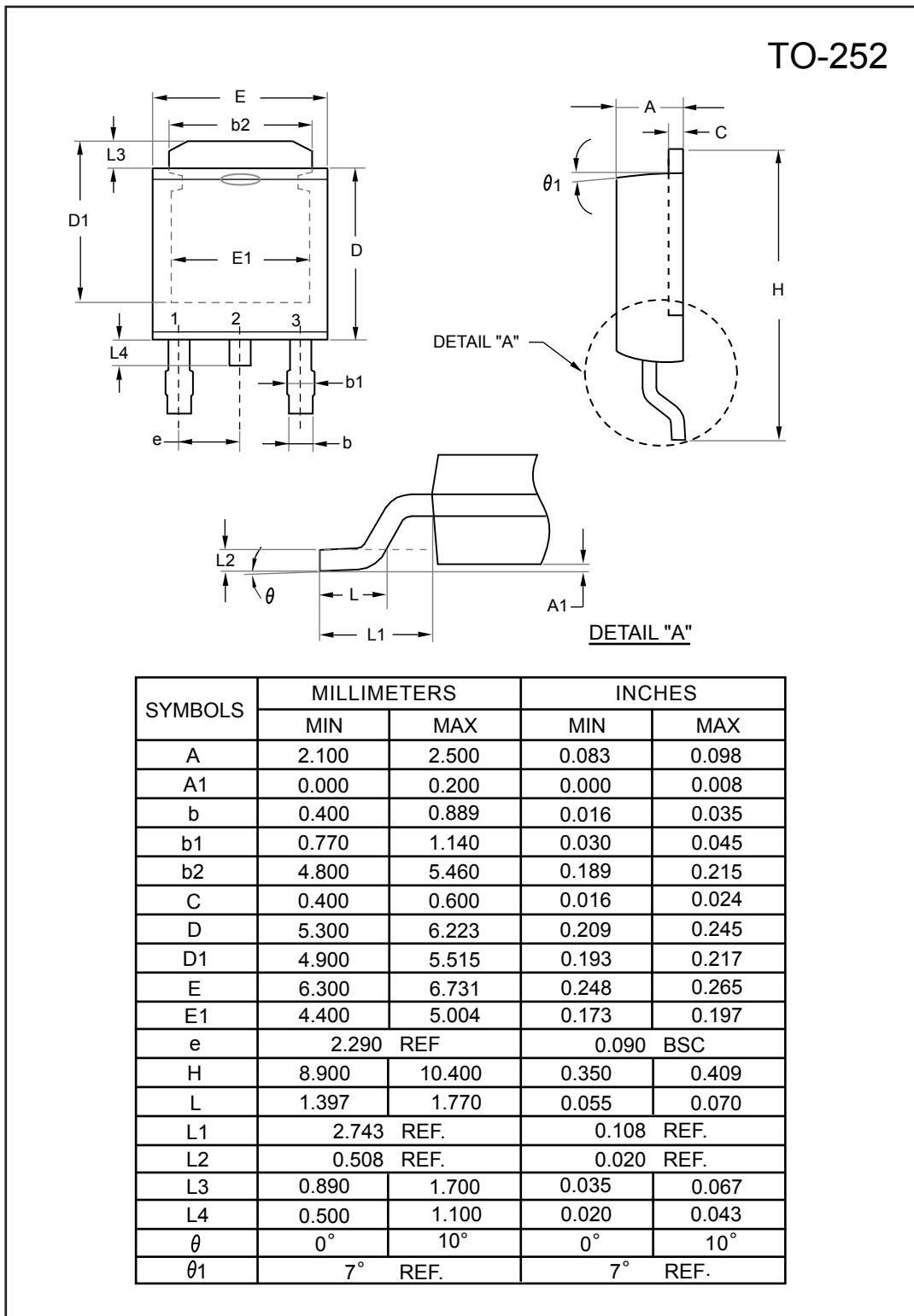
TO-251



SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.100	2.500	0.083	0.098
A1	0.350	0.650	0.014	0.026
B	0.400	0.800	0.016	0.031
B1	0.650	1.050	0.026	0.041
B2	0.500	0.900	0.020	0.035
C	0.400	0.600	0.016	0.024
D	5.300	5.700	0.209	0.224
D1	4.900	5.300	0.193	0.209
D2	6.700	7.300	0.264	0.287
D3	7.000	8.000	0.276	0.315
H	13.700	15.300	0.539	0.602
E	6.300	6.700	0.248	0.264
E1	4.600	4.900	0.181	0.193
E2	4.800	5.200	0.189	0.205
L	1.300	1.700	0.051	0.067
L1	1.400	1.800	0.055	0.071
L2	0.500	0.900	0.020	0.035
P	2.300 BSC		0.091 BSC	

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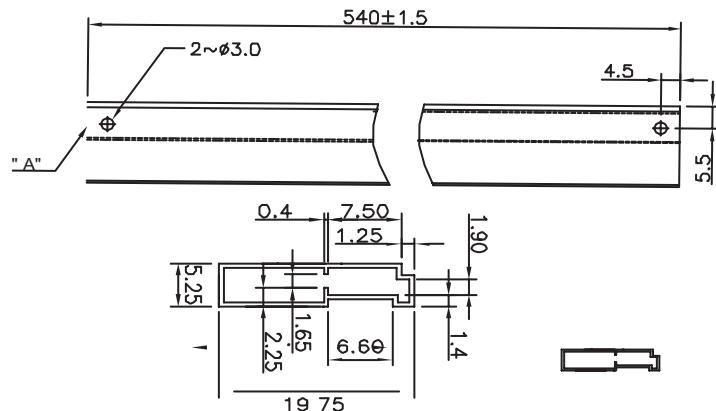
PACKAGE OUTLINE DIMENSIONS



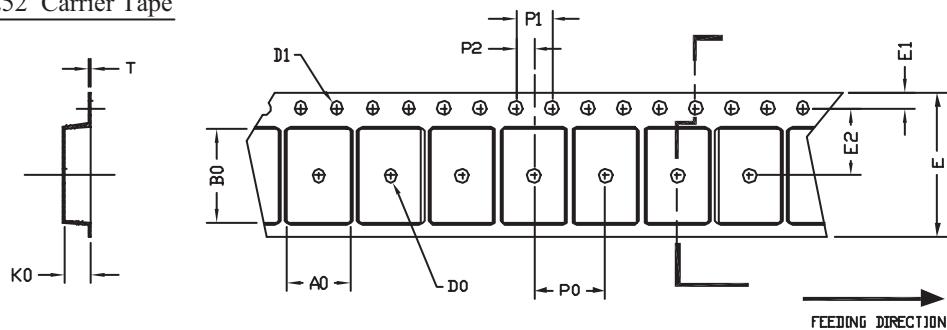
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TO251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



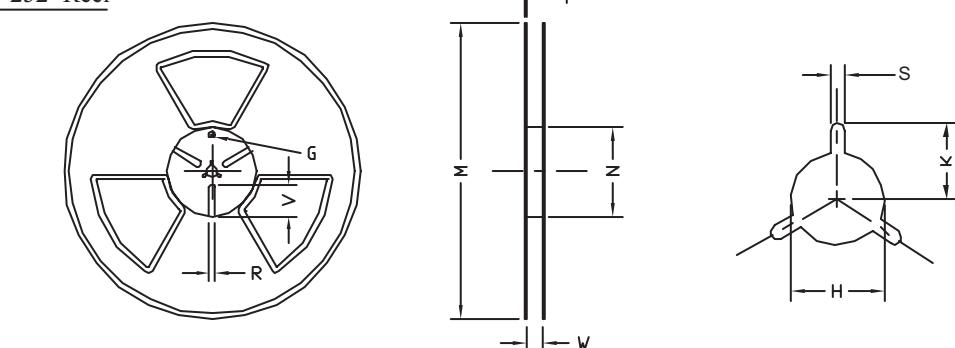
TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.80 ±0.1	10.3 ±0.1	2.50 ±0.1	ψ 2	ψ 1.5 + 0.1 - 0	16.0	0.3±	0.1±	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15 ±0.05

TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	ψ 330	ψ 330 ± 0.5	ψ 97 ± 1.0	17.0 + 1.5 - 0	2.2	ψ 13.0 + 0.5 - 0.2	10.6	2.0 ± 0.5	---	---	---